

# Graphene on SrTiO<sub>3</sub>

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We comment on a recent article involving carrier transport through graphene on SrTiO<sub>3</sub> substrates by considering relative contributions of Coulomb and resonant impurity scattering to graphene resistivity. We establish that charged impurity scattering must dominate graphene transport as the charge neutrality point is approached by lowering the carrier density, and in the higher density regime away from the neutrality point a dual model including both charged impurities and resonant defects gives an excellent description of graphene transport on SrTiO<sub>3</sub> substrates.

In a recent paper [1] Couto *et al.* claim that their measured conductivity,  $\sigma(n)$ , of graphene on SrTiO<sub>3</sub> substrates (1) cannot be explained by the standard model [2, 3] of Coulomb disorder in the environment, which has earlier been found to provide a reasonable theoretical description for graphene transport on SiO<sub>2</sub> substrates from many different groups [4] as well as on several other substrates [5], and (2) can be explained quantitatively by a so-called “resonant scattering” model [6], which gives the following expression for the carrier density ( $n$ ) dependence of the conductivity  $\sigma$ :  $\sigma(n) = \frac{2e^2}{\pi h} \frac{n}{n_i} \ln^2(\sqrt{n\pi R^2})$ , where  $n_i, R$  are respectively the concentration and the range of the short-range resonant scattering defects in graphene. In this Comment, we point out that both of these claims in Ref. [1] are unfounded and misleading, if not incorrect.

First, regarding the item (2) above, a conductivity formula with  $\sigma \sim \frac{n}{n_i} \ln^2(\sqrt{n/n_0})$  cannot, by definition, even qualitatively account for the most important aspect of graphene transport, namely, the existence of the low-density minimum conductivity for a finite range of density around the Dirac (i.e. charge neutrality) point. Thus, the resonant scattering model, even in the most favorable circumstances, can only be a rather phenomenological data-fitting scheme for  $\sigma(n)$  in an intermediate density range  $n_c < n < n_0$  where  $n_c$  defines the density regime for the graphene minimum conductivity plateau around the Dirac point (taken to be at  $n = 0$  in this comment) and  $n_0 \equiv (\pi R^2)^{-1}$ . Second, the authors of Ref. [1] provide absolutely no physical evidence for the existence of these “resonant scattering” short-range atomic defects (with  $n_i \sim 3 \times 10^{11} \text{ cm}^{-2}$ ) which appear invisible except for providing an intermediate-density phenomenological fit to their conductivity data. At best, Ref. [1] provides a weak circumstantial evidence that the presence of resonant scattering may be sufficient, but by no means necessary, for describing the intermediate density behavior of  $\sigma(n)$  on SrTiO<sub>3</sub> substrates.

The only argument made in [1] against the applicability of Coulomb disorder to their data is the apparent non-existence of any strong temperature dependence of  $\sigma(n)$  which, it is claimed in [1], should follow naturally from the strong temperature dependence of the lattice dielec-

tric constant ( $\kappa$ ) of SrTiO<sub>3</sub> which undergoes a paraelectric to a ferroelectric lattice instability with the lowering of temperature. While the apparent absence of any temperature dependence of  $\sigma(n)$  in Ref. [1] is indeed puzzling for graphene on SrTiO<sub>3</sub>, given the strong variation in the background  $\kappa(T)$ , we disagree with the premature conclusion reached in Ref. [1] that this single observation by itself definitively proves the absence of any effective long-range Coulomb scattering by random charged impurities in the system. This is particularly true in view of the (almost essential) necessity for the presence of Coulomb disorder in order to provide a reasonable explanation for the graphene minimum conductivity phenomenon [2–5] around the charge neutrality point (which is, of course, also observed in Ref. [1]). We assert that the standard model for graphene transport [2, 3] with Coulomb disorder can easily and successfully provide a perfect phenomenological fit to the  $\sigma(n)$  data of Ref. [1] with the single assumption of a variable background charged impurity density with varying temperature. The assumption of a temperature-dependent charged impurity density for SrTiO<sub>3</sub> substrates is not an arbitrary data fitting ploy (which in any case is not refuted by any information presented in Ref. [1]) because the complicated lattice ferroelectric properties of SrTiO<sub>3</sub> leading to the strong functional dependence of the dielectric constant on temperature may very well also produce a temperature dependent charged impurity density increasing strongly with decreasing temperature just as the actual carrier density in graphene on SrTiO<sub>3</sub> increases rapidly with decreasing temperature at a fixed gate voltage (see Fig. 2 in the Supplementary Information of Ref. [1]). Thus, if getting agreement with the experimental data of Ref. [1] is the sole criterion for the validity of the underlying physical scattering mechanism in the system, then Coulomb disorder does a better job than the resonant scattering model since it also provides an explanation for the minimum conductivity around the Dirac point with the single assumption of a temperature-dependent background Coulomb disorder.

It is entirely possible that the transport data of Ref. [1] is best described by a combination of Coulomb disorder and resonant scattering, where the low-density minimum

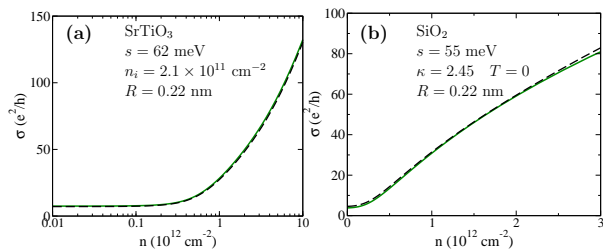


FIG. 1. (a) Fits to the  $\sigma(n)$  data in Ref. [1] (graphene on SrTiO<sub>3</sub>) including Coulomb impurity  $n_{imp}$  and resonant impurity  $n_i$ . The solid (dashed) line is for the temperature  $T = 0.25$  (50) K,  $\kappa = 2000$  (200) and  $n_{imp} = 2 \times 10^{14}$  ( $1 \times 10^{13}$  cm<sup>-2</sup>). (b) Fits to the  $\sigma(n)$  data in Ref. [7] (graphene on SiO<sub>2</sub>). The solid line is the fit including  $n_{imp} = 5.5 \times 10^{11}$  cm<sup>-2</sup> and zero-range disorder  $n_{sd}V_0^2 = 1.3$  (eV·Å)<sup>2</sup>. The dashed line is the fit including Coulomb impurity  $n_{imp} = 3 \times 10^{11}$  cm<sup>-2</sup> and resonant impurity  $n_i = 1.0 \times 10^{11}$  cm<sup>-2</sup>. Note that we use the theory presented in Ref. [3],  $s$  denotes the potential fluctuation associated with the puddles induced by Coulomb disorder [8] and the average distance of the charged impurity from the graphene sheet used in (a) and (b) is  $d = 1$  Å.

conductivity arises from the Coulomb disorder and the intermediate (sublinear in) density conductivity arises from resonant scattering. In Fig.1 we show our best theoretical fits to the data of Ref. [1] assuming dual independent scattering by charged impurity and resonant scattering centers. The fact that we get excellent agreement over the whole density range of the experimental data indicates that our dual scattering model is a more reasonable description than the pure resonant scattering model proposed in Ref. [1]. (We have obtained similar good theoretical fits to the existing graphene on SiO<sub>2</sub> conductivity data too, which are also shown in Fig. 1.) We believe that much more experimental work would be necessary, with possible direct spectroscopic signature of the resonant scattering defects and the associated midgap states, before the existence of resonant scatter-

ing in graphene can be accepted beyond any reasonable doubt. It is, however, important to emphasize that since  $\sigma_r/\sigma_c \sim \ln^2(\sqrt{n/n_0})$ , where  $\sigma_{r,c}$  are the resonant scattering and Coulomb scattering induced conductivity respectively, Coulomb disorder, with  $\sigma_c \sim n$  [2], must necessarily dominate graphene resistivity as one approaches the  $n \rightarrow 0$  charge neutrality point. This key physics is missing in the analysis of Ref. [1].

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